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## FQPF13N50CF N-Channel QFET<sup>®</sup> FRFET<sup>®</sup> MOSFET

## 500 V, 13 A, 540 m $\Omega$

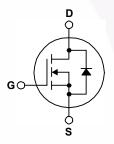
#### Features

- + 13 A, 500 V,  $R_{DS(on)}$  = 540 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_{D}$  = 6.5 A
- Low Gate Charge (Typ. 43 nC)
- Low Crss (Typ. 20 pF)
- 100% Avalanche Tested
- Fast Recovery Body Diode (Typ. 100 ns)

### Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.





#### MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol		Parameter	FQPF13N50CF	Unit	
V <sub>DSS</sub>	Drain to Source Voltage			500	V
I <sub>D</sub>	Desia Current	- Continuous (T <sub>C</sub> = 25°C)		13	A
	Drain Current	- Continuous (T <sub>C</sub> = 100	0°C)	8	A
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	52	A
V <sub>GSS</sub>	Gate to Source Voltage			± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Er	nergy	(Note 2)	530	mJ
I <sub>AR</sub>	Avalanche Current		(Note 1)	13	A
E <sub>AR</sub>	Repetitive Avalanche Energy		(Note 1)	19.5	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	4.5	V/ns
P <sub>D</sub>	Devuer Dissinction	(T <sub>C</sub> = 25 <sup>o</sup> C)		48	W
	Power Dissipation	- Derate above 25°C		0.39	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C
TL	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300	°C

### Thermal Characteristics

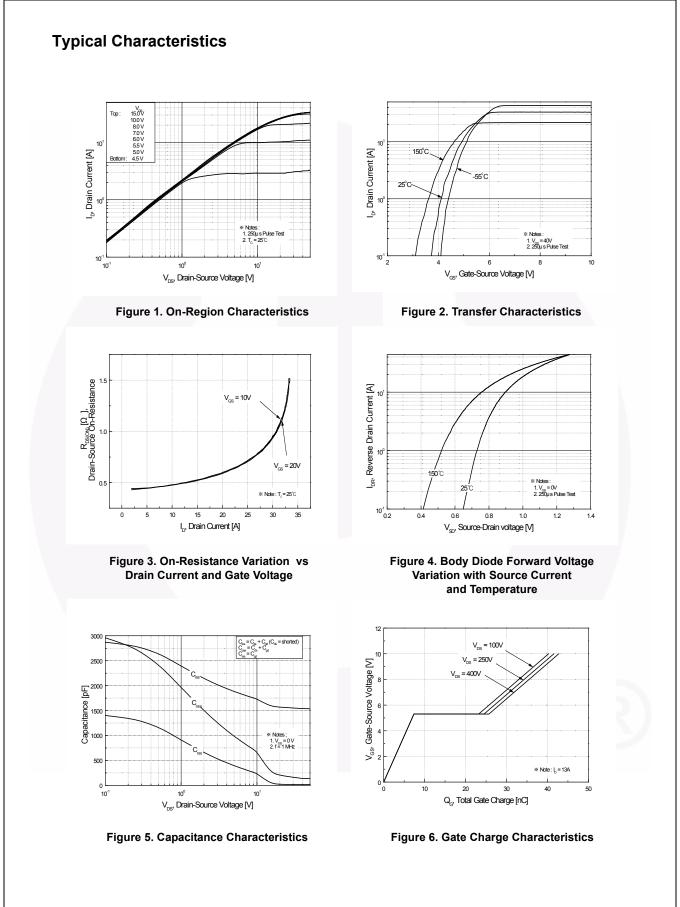
Symbol	Parameter	FQPF13N50CF	Unit	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	2.58	°C/W	
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	- 0/11	

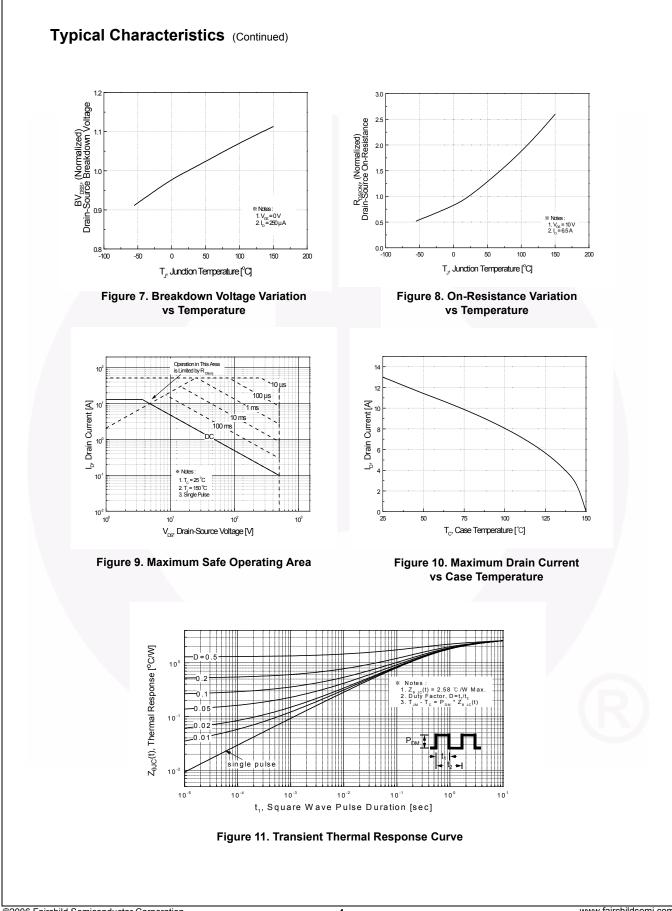
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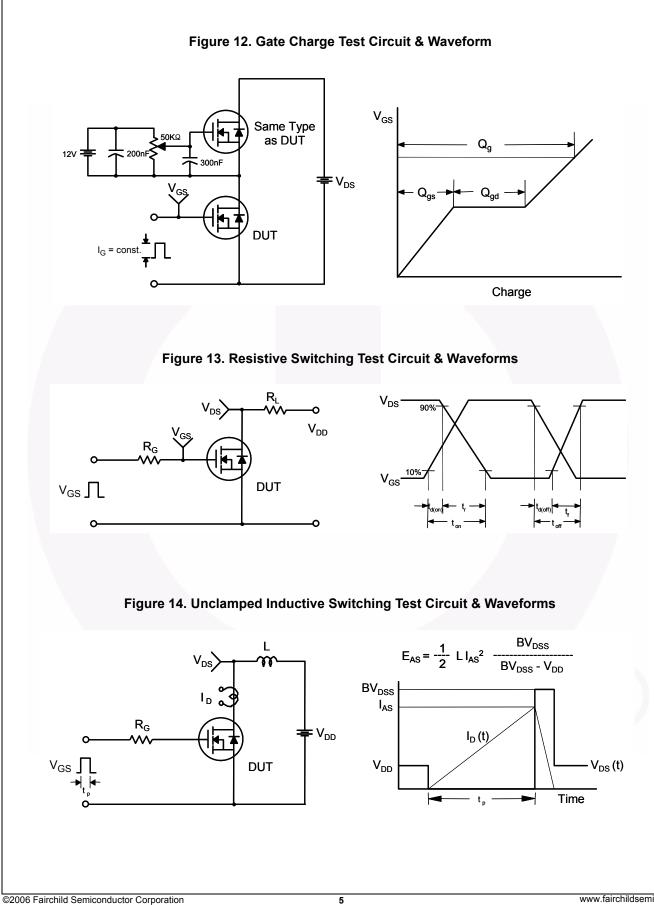
June 2014

Device MarkingDeviceFQPF13N50CFFQPF13N50CF		Device	Package Reel Size		Tape Width		Quantity	
		TO-220F Tube		N/A		50 units		
Electri	cal Chara	cteristics T <sub>C</sub> = 25°C ur	nless otherwise noted.					
Symbol		Parameter	Test Conditi	ons	Min	Тур	Max	Unit
Off Cha	aracteristic	s						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage		V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA		500			V
$\Delta BV_{DSS}$	Breakdown Voltage Temperature Coeffi-		$I_D = 250 \ \mu$ A, Referenced to 25°C			0.5		V/°C
/∆T <sub>J</sub>	cient		V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V				10	
I <sub>DSS</sub>	Zero Gate Vo	oltage Drain Current	$V_{DS} = 300 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 400 \text{ V}, T_C = 125^{\circ}\text{C}$				10 100	μΑ
10005	Gate-Body Leakage Current, Forward		$V_{\rm DS} = 400$ V, $V_{\rm C} = 123$ C $V_{\rm GS} = 30$ V, $V_{\rm DS} = 0$ V				100	μA nA
I <sub>GSSF</sub> I <sub>GSSR</sub>		eakage Current, Reverse	$V_{GS} = -30 V, V_{DS} = 0 V$	/			-100	nA
GSSR			rgs corr, rps cr				-100	
On Cha	racteristic	S						
V <sub>GS(th)</sub>	Gate Threshold Voltage		$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		2.0		4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 6.5 A			0.43	0.54	Ω
9 <sub>FS</sub>	Forward Transconductance		V <sub>DS</sub> = 40 V, I <sub>D</sub> = 6.5 A			15		S
Dynam	ic Characte	eristics					1	
C <sub>iss</sub>	Input Capacitance		V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,			1580	2055	pF
C <sub>oss</sub>	Output Capa		f = 1.0 MHz			180	235	pF
C <sub>rss</sub>	Reverse Tra	nsfer Capacitance				20	25	pF
Switchi	ing Charac	teristics						
t <sub>d(on)</sub>	Turn-On Dela		V <sub>DD</sub> = 250 V, I <sub>D</sub> = 13 A			25	60	ns
t <sub>r</sub>	Turn-On Rise	e Time	$R_{G} = 25 \Omega$	·,		100	210	ns
t <sub>d(off)</sub>	Turn-Off Dela	ay Time	(Note 4)			130	270	ns
t <sub>f</sub>	Turn-Off Fall	Time				100	210	ns
Qg	Total Gate C	harge	V <sub>DS</sub> = 400 V, I <sub>D</sub> = 13 A	<b>.</b> ,		43	56	nC
Q <sub>gs</sub>	Gate-Source	Charge	V <sub>GS</sub> = 10 V	ſ		7.5		nC
Q <sub>gd</sub>	Gate-Drain C	Charge	(Note 4)			18.5		nC
Duciu 0			Mariana Datia	_				
brain-S	1	te Characteristics and ontinuous Drain-Source Diode					13	A
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current					52	A	
V <sub>SD</sub>		e Diode Forward Voltage	$V_{GS} = 0 V, I_{S} = 13 A$				1.4	V
t <sub>rr</sub>	Reverse Red	•	$V_{GS} = 0 V, I_S = 13 A,$			100	160	ns
Q <sub>rr</sub>		covery Charge	$dI_{\rm F}$ / dt = 100 A/µs			0.35		μC
	1	, ,				1		<u> </u>

4. Essentially independent of operating temperature.







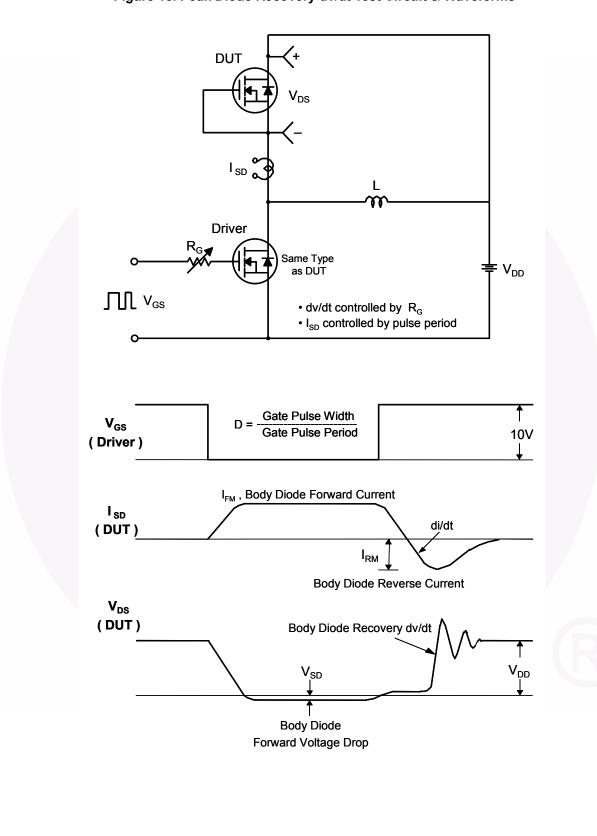
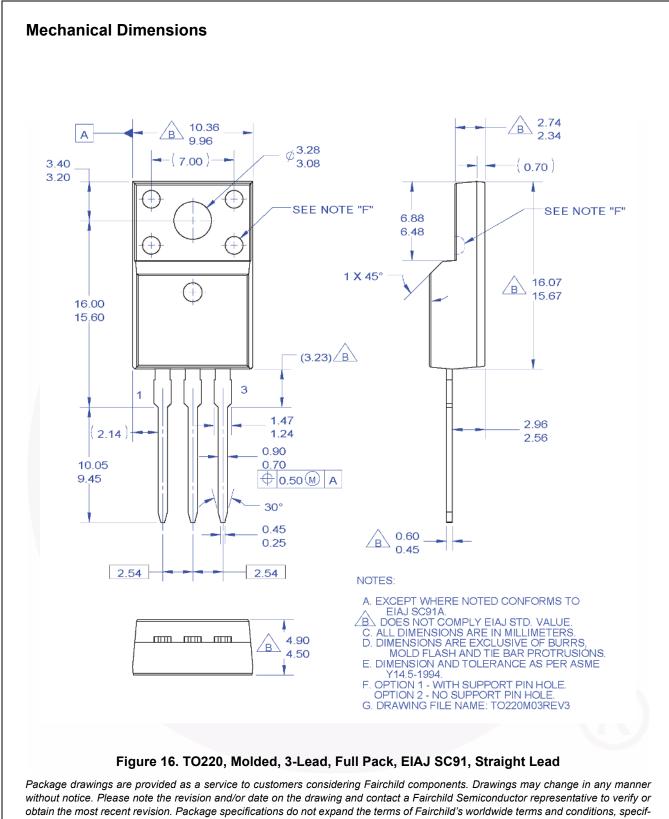


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



ically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN\_TF220-003



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